



40V N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(ON)}	I _D T _A = +25°C	
40V	0.05Ω @ $V_{GS} = 10V$	7A	

Description

This new generation MOSFET has been designed to minimize the onstate resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- DC-DC Converters
- Audio Output Stages
- · Relay and Solenoid driving
- Motor Control

Features

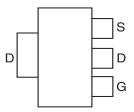
- Low On-Resistance
- Fast Switching Speed
- Low Threshold
- Low Gate Drive
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Available

Mechanical Data

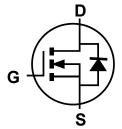
- Case: SOT223
- Case Material: Molded Plastic, UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin annealed over Copper lead frame.
 Solderable per MIL-STD-202, Method 208 <a>®3
- Weight: 0.112 grams (approximate)







Pin Out - Top View



Equivalent Circuit

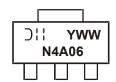
Ordering Information (Note 4 & 5)

Part Number	Compliance	Case	Packaging
ZXMN4A06GQTA	Automotive	SOT223	1,000/Tape & Reel
ZXMN4A06GQTC	Automotive	SOT223	4,000/Tape & Reel

Note:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/quality/product_grade_definitions/.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



O!! = Manufacturer's Marking N4A06 = Marking Code YWW = Date Code Marking Y = Year (ex: 3 = 2013) WW = Week (01 - 53)



Maximum Ratings ($@T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage		V_{DSS}	40	V	
Gate-Source Voltage			V _{GS}	±20	V
		(Note 7)		7	
Continuous Drain Current	$V_{GS} = 10V$	$T_A = +70^{\circ}C \text{ (Note 7)}$	I_{D}	5.6	Α
		(Note 6)		5	
Pulsed Drain Current	V _{GS} = 10V	(Note 8)	I _{DM}	22	Α
Continuous Source Current (Body diode) (Note 7)		(Note 7)	I _S	5.4	Α
Pulsed Source Current (Body diode) (Note 8)		I _{SM}	22	Α	

Thermal Characteristics ($@T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Power Dissipation	(Note 6)		2 16	W	
Linear Derating Factor	(Note 7)	PD	3.9 31	mW/°C	
Thermal Resistance, Junction to Ambient	(Note 6)	R _{0JA}	62.5	°C/W	
Thermal Resistance, sunction to Ambient	(Note 7)	NejA	32.2		
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C	

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

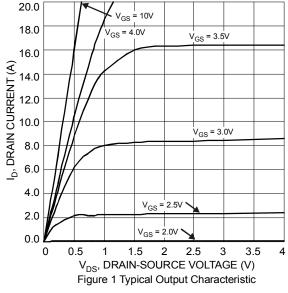
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage	BV _{DSS}	40	_	_	V	$I_D = 250 \mu A, V_{GS} = 0 V$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1	μA	V _{DS} = 40V, V _{GS} = 0V	
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 20V$, $V_{DS} = 0V$	
ON CHARACTERISTICS	ON CHARACTERISTICS						
Gate Threshold Voltage	V _{GS(th)}	1			V	$I_D = 250 \mu A, V_{DS} = V_{GS}$	
Static Drain-Source On-Resistance (Note 9)	D			0.05	Ω	V _{GS} = 10V, I _D = 4.5A	
Static Dialit-Source Off-Nesistatice (Note 9)	R _{DS(ON)}	_		0.075	32	$V_{GS} = 4.5V$, $I_D = 3.2A$	
Forward Transconductance (Notes 11)	g _{fs}	_	8.7		S	V _{DS} = 15V, I _D = 2.5A	
Diode Forward Voltage (Note 9)	V_{SD}	_	0.8	0.95	V	I _S = 2.5A, V _{GS} = 0V, T _J = +25°C	
Reverse recovery time (Note 11)	t _{rr}		14.5	_	ns	$I_F = 2.5A$, di/dt = 100A/ μ s, $T_J = +25$ °C	
Reverse recovery charge (Note 11)	Qrr	_	7.8	_	nC		
DYNAMIC CHARACTERISTICS (Note 10)							
Input Capacitance	C _{iss}	_	746	_	pF	V _{DS} = 40V, V _{GS} = 0V f = 1MHz	
Output Capacitance	Coss	_	93		pF		
Reverse Transfer Capacitance	C _{rss}	_	60	_	pF	1 - 1141112	
Total Gate Charge (Note 11)	Q_g	_	19	_	nC	14 001/14 101/	
Gate-Source Charge (Note 11)	Q_{gs}	_	2.3	_	nC	V_{DS} = 30V, V_{GS} = 10V, I_{D} = 2.5A (refer to test circuit)	
Gate-Drain Charge (Note 11)	Q_{gd}	_	4.1	_	nC		
Turn-On Delay Time (Note 11)	t _{D(on)}	_	3.4	_	ns	V_{DD} = 30V, V_{GS} = 10V I_{D} = 2.5A, $R_{G} \approx 6\Omega$ (refer to test circuit)	
Turn-On Rise Time (Note 11)	t _r	_	2.8	_	ns		
Turn-Off Delay Time (Note 11)	t _{D(off)}	_	20	_	ns		
Turn-Off Fall Time (Note 11)	t _f	_	7.7	_	ns		

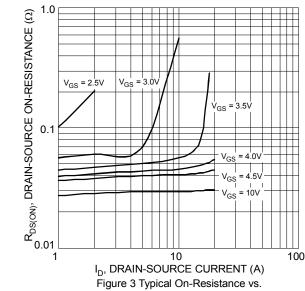
Notes:

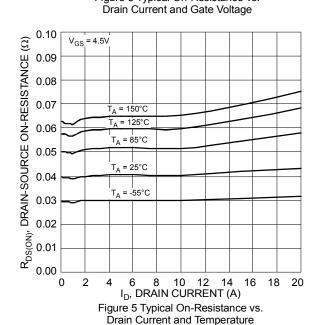
- 6. For a device surface mounted on 25mm x 25mm FR-4 PCB with high coverage of single sided 1oz copper, in still air conditions. 7. For a device surface mounted on FR-4 PCB measured at t≤5 secs. 8. Repetitive rating 25mm x 25mm FR4 PCB, D = 0.05, pulse width 10µs pulse width limited by maximum junction temperature.

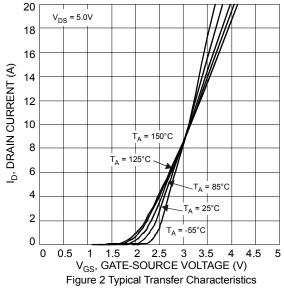
- 9. Measured under pulsed conditions. Pulse width \leq 300 μ s; duty cycle \leq 2%.
- 10. Switching characteristics are independent of operating junction temperatures.
- 11. For design aid only, not subject to production testing.

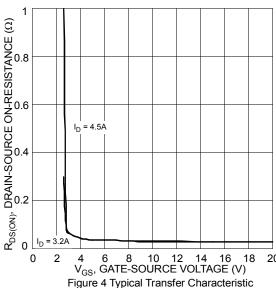












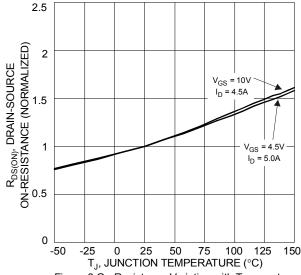
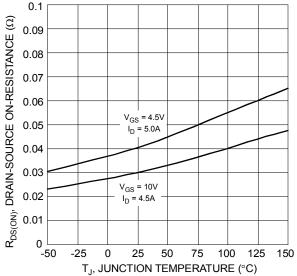
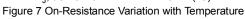
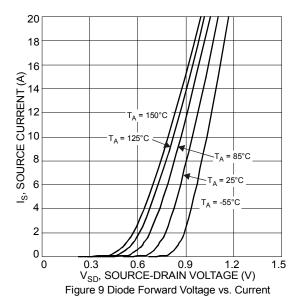


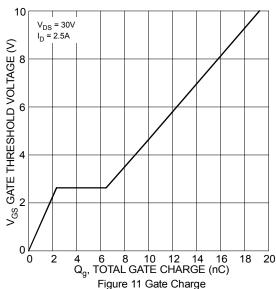
Figure 6 On-Resistance Variation with Temperature

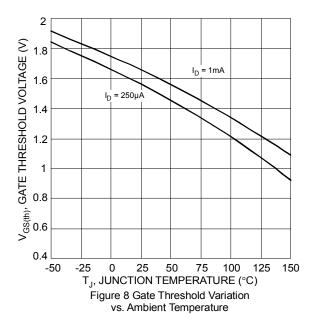


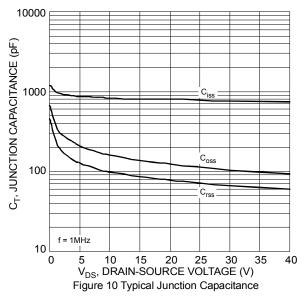


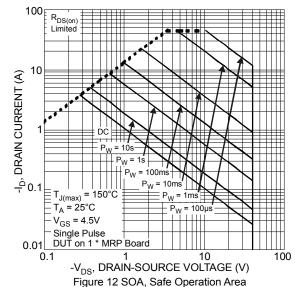




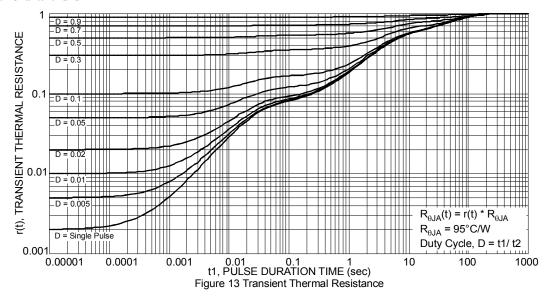






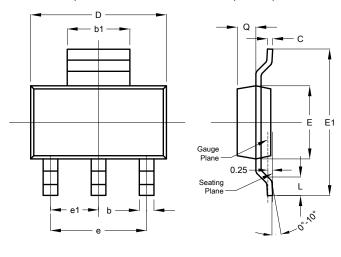




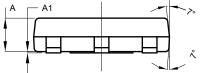


Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.

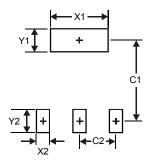


SOT223					
Dim	Min	Max	Тур		
Α	1.55	1.65	1.60		
A1	0.010	0.15	0.05		
b1	2.90	3.10	3.00		
b2	0.60	0.80	0.70		
С	0.20	0.30	0.25		
D	6.45	6.55	6.50		
Е	3.45	3.55	3.50		
E1	6.90	7.10	7.00		
е	_	-	4.60		
e1			2.30		
L	0.85	1.05	0.95		
Q	0.84	0.94	0.89		
All Dimensions in mm					



Suggested Pad Layout

 $Please see AP02001 \ at \ http://www.diodes.com/datasheets/ap02001.pdf \ for \ latest \ version.$



Dimensions	Value (in mm)		
X1	3.3		
X2	1.2		
Y1	1.6		
Y2	1.6		
C1	6.4		
C2	2.3		



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